

Title (en)

SEMICONDUCTOR WAFER TREATMENT SOLUTION AND PRODUCTION METHOD FOR SAME

Title (de)

LÖSUNG ZUR BEHANDLUNG VON HALBLEITERWAFERN UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)

SOLUTION DE TRAITEMENT DE TRANCHE DE SEMI-CONDUCTEUR ET SON PROCÉDÉ DE PRÉPARATION

Publication

EP 4269656 A1 20231101 (EN)

Application

EP 21898008 A 20211125

Priority

- JP 2020196348 A 20201126
- JP 2021043087 W 20211125

Abstract (en)

The present invention provides a semiconductor wafer treatment liquid, the treatment liquid including at least one hypohalite ion, and at least one anion species selected from halate ion, halite ion and halide ion, wherein at least one of the anion species has a content of 0.30 mol/L or more and 6.00 mol/L or less relative to the treatment liquid.

IPC 8 full level

C23F 1/32 (2006.01); **H01L 21/308** (2006.01)

CPC (source: EP KR US)

C23F 1/38 (2013.01 - EP KR); **C23F 1/40** (2013.01 - EP KR US); **H01L 21/32134** (2013.01 - EP KR US)

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

Designated validation state (EPC)

KH MA MD TN

DOCDB simple family (publication)

US 2022411937 A1 20221229; CN 116529421 A 20230801; EP 4269656 A1 20231101; JP WO2022114036 A1 20220602; KR 20230111234 A 20230725; TW 202221104 A 20220601; WO 2022114036 A1 20220602

DOCDB simple family (application)

US 202117642059 A 20211125; CN 202180079747 A 20211125; EP 21898008 A 20211125; JP 2021043087 W 20211125; JP 2022565395 A 20211125; KR 20237021381 A 20211125; TW 110144147 A 20211126